

ANALOG UNUS 1.0 V to 3.3 V, 2.3 1. DEVICES SPDT Switch/2:1 Mux in Tiny SC70 Package

ADG779

FEATURES

1.8 V to 5.5 V single supply 2.5 Ω on resistance 0.75 Ω on-resistance flatness -3 dB bandwidth >200 MHz Rail-to-rail operation 6-lead SC70 package **Fast switching times**

ton 20 ns toff 6 ns

Typical power consumption (<0.01 μW) TTL/CMOS compatible

APPLICATIONS

Battery-powered systems Communication systems Sample hold systems **Audio signal routing** Video switching Mechanical reed relay replacements

GENERAL DESCRIPTION

The ADG779 is a monolithic CMOS SPDT (single-pole, double-throw) switch. This switch is designed on a submicron process that provides low power dissipation yet gives high switching speed, low on resistance, and low leakage currents.

The ADG779 operates from a single supply range of 1.8 V to 5.5 V, making it ideal for use in battery-powered instruments and with the new generation of DACs and ADCs from Analog Devices, Inc.

Each switch of the ADG779 conducts equally well in both directions when on. The ADG779 exhibits break-before-make switching action.

Because of the advanced submicron process, -3 dB bandwidth of greater than 200 MHz can be achieved.

The ADG779 is available in a 6-lead SC70 package.

FUNCTIONAL BLOCK DIAGRAM

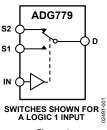


Figure 1.

PRODUCT HIGHLIGHTS

- Tiny 6-Lead SC70 Package.
- 1.8 V to 5.5 V Single-Supply Operation. The ADG779 offers high performance, including low on resistance and fast switching times, and is fully specified and guaranteed with 3 V and 5 V supply rails.
- Very Low R_{ON} (5 Ω max at 5 V, 10 Ω max at 3 V). At 1.8 V operation, R_{ON} is typically 40 Ω over the temperature range.
- On-Resistance Flatness ($R_{FLAT (ON)}$) (0.75 Ω typ).
- −3 dB Bandwidth > 200 MHz.
- Low Power Dissipation. CMOS construction ensures low power dissipation.
- 14 ns Switching Times.

ADG779

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REVISION HISTORY

10/05—Rev. 0 to Rev. A

Updated Format	Universal
Changes to Table 1	3
Changes to Table 2	
Changes to Table 3	
Changes to Terminology Section	
Changes to Ordering Guide	

7/01—Revision 0: Initial Version

SPECIFICATIONS

 V_{DD} = 5 V \pm 10%, GND = 0 V^{1}

Table 1.

B Version					
	−40°C to				
Parameter	25°C	+85°C	Unit	Test Conditions/Comments	
ANALOG SWITCH					
Analog Signal Range		$0VtoV_{DD}$	V		
On Resistance (R _{ON})	2.5		Ω typ	$V_S = 0 \text{ V to } V_{DD}$, $I_S = -10 \text{ mA}$, see Figure 12	
	5	6	Ω max		
On-Resistance Match Between Channels (ΔR_{ON})	0.1		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
		0.8	Ω max		
On-Resistance Flatness (R _{FLAT (ON)})	0.75		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$	
		1.2	Ω max		
LEAKAGE CURRENTS ²				$V_{DD} = 5.5 \text{ V}$	
Source Off Leakage Is (Off)	±0.01	±0.05	nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V}, \text{ see Figure 13}$	
Channel On Leakage I _D , I _S (On)	±0.01	±0.05	nA typ	$V_S = V_D = 1 \text{ V, or } V_S = V_D = 4.5 \text{ V, see Figure 14}$	
DIGITAL INPUTS					
Input High Voltage, V _{INH}		2.4	V min		
Input Low Voltage, V _{INL}		0.8	V max		
Input Current					
lint or linh	0.005		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$	
		±0.1	μA max		
DYNAMIC CHARACTERISTICS ²					
ton	14		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
		20	ns max	$V_S = 3 \text{ V}$, see Figure 15	
toff	3		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
		6	ns max	$V_S = 3 \text{ V, see Figure 15}$	
Break-Before-Make Time Delay, t _D	8		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$	
		1	ns min	$V_{S1} = V_{S2} = 3 \text{ V, see Figure 16}$	
Off Isolation	-67		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	
	-87		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 17	
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$	
	-82		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 18	
Bandwidth –3 dB	200		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$, see Figure 19	
C _s (Off)	7		pF typ	f = 1 MHz	
C_D , C_S (On)	27		pF typ	f = 1 MHz	
POWER REQUIREMENTS				V _{DD} = 5.5 V	
				Digital Inputs = 0 V or 5 V	
I _{DD}	0.001		μA typ		
		1.0	μA max		

 $^{^1}$ Temperature range is B Version, -40°C to $+85^\circ\text{C}.$ 2 Guaranteed by design, not subject to production test.

ADG779

 V_{DD} = 3 V ± 10%, GND = 0 V¹

Table 2.

B Version				
_		−40°C to		
Parameter	25°C	+85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$0 V \text{ to } V_{DD}$	V	
On Resistance (R _{ON})	6	7	Ωtyp	$V_S = 0 \text{ V to } V_{DD}$, $I_S = -10 \text{ mA}$, see Figure 12
		10	Ω max	
On-Resistance Match Between Channels (ΔR_{ON})	0.1		Ω typ	$V_S = 0 \text{ V to } V_{DD}$, $I_S = -10 \text{ mA}$
		8.0	Ω max	
On-Resistance Flatness (R _{FLAT (ON)})	2.5		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS ²				$V_{DD} = 3.3 \text{ V}$
Source Off Leakage Is (Off)	±0.01	±0.05	nA typ	$V_S = 3 \text{ V}/1 \text{ V}, V_D = 1 \text{ V}/3 \text{ V}, \text{ see Figure 13}$
Channel On Leakage ID, Is (On)	±0.01	±0.05	nA typ	$V_S = V_D = 1 \text{ V, or } V_S = V_D = 3 \text{ V, see Figure 14}$
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.0	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current				
I _{INL} or I _{INH}	0.005		μA typ	$V_{IN} = V_{INL}$ or V_{INH}
		±0.1	μA max	
DYNAMIC CHARACTERISTICS ²				
ton	16		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		24	ns max	$V_s = 2 V$, see Figure 15
toff	4		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		7	ns max	V _S = 2 V, see Figure 15
Break-Before-Make Time Delay, t _D	8		ns typ	$R_L = 300 \Omega, C_L = 35 pF$
		1	ns min	$V_{S1} = V_{S2} = 2 \text{ V, see Figure 16}$
Off Isolation	-67		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$
	-87		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 17
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$
	-82		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$, see Figure 18
Bandwidth –3 dB	200		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$, see Figure 19
C _s (Off)	7		pF typ	f = 1 MHz
C _D , C _s (On)	27		pF typ	f = 1 MHz
POWER REQUIREMENTS				$V_{DD} = 3.3 \text{ V}$
				Digital Inputs = 0 V or 3 V
IDD	0.001		μA typ	·
	1	1.0	μA max	

 $^{^1}$ Temperature range is B Version, -40°C to +85°C. 2 Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 3.

1 autc 3.	
Parameter	Rating
V _{DD} to GND	−0.3 V to +7 V
Analog, Digital Inputs ¹	$-0.3 \text{ V to V}_{DD} + 0.3 \text{ V or } 30 \text{ mA},$ whichever occurs first
Peak Current, S or D	100 mA (pulsed at 1 ms, 10% duty cycle max)
Continuous Current, S or D	30 mA
Operating Temperature Range	
Industrial (B Version)	−40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
SC70 Package, Power Dissipation	315 mW
θ_{JA} Thermal Impedance	332°C/W
θ_{JC} Thermal Impedance	120°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C
Reflow Soldering (Pb-free)	
Peak Temperature	260 (+0/-5)°C
Time at Peak Temperature	10 sec to 40 sec

 $^{^{\}rm 1}$ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 4. Truth Table

ADG779 IN	Switch S1	Switch S2
0	On	Off
1	Off	On

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



PIN CONFIGURATION AND FUNCTION DESCRIPTIONS



Figure 2. Pin Configuration

Table 5. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	IN	Logic Control Input.
2	V_{DD}	Most Positive Power Supply Potential.
3	GND	Ground (0 V) Reference.
4	S1	Source Terminal. Can be an input or an output.
5	D	Drain Terminal. Can be an input or an output.
6	S2	Source Terminal. Can be an input or an output.

TERMINOLOGY

 V_{DD}

Most positive power supply potential.

 \mathbf{I}_{DD}

Positive supply current.

GND

Ground (0 V) reference.

S

Source terminal. Can be an input or an output.

D

Drain terminal. Can be an input or an output.

IN

Logic control input.

 $V_D(V_S)$

Analog voltage on drain (D) and source (S) terminals.

Ron

Ohmic resistance between the D and S.

R_{FLAT} (ON)

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured.

 ΔR_{ON}

On-resistance mismatch between any two channels.

Is (Off)

Source leakage current with the switch off.

ID (Off)

Drain leakage current with the switch off.

 I_D , I_S (On)

Channel leakage current with the switch on.

 V_{INI}

Maximum input voltage for Logic 0.

 V_{INH}

Minimum input voltage for Logic 1.

 $I_{\rm INL}\left(I_{\rm INH}\right)$

Input current of the digital input.

Cs (Off)

Off switch source capacitance. Measured with reference to ground.

C_D (Off)

Off switch drain capacitance. Measured with reference to ground.

C_D, C_s (On)

On switch capacitance. Measured with reference to ground.

CIN

Digital input capacitance.

 $t_{\rm ON}$

Delay time between the 50% and 90% points of the digital input and switch on condition.

toff

Delay time between the 50% and 90% points of the digital input and switch off condition.

tBBM

On or off time measured between the 80% points of both switches when switching from one to another.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during on/off switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another because of parasitic capacitance.

-3 dB Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch.

THD + N

The ratio of harmonic amplitudes plus noise of a signal to the fundamental.

TYPICAL PERFORMANCE CHARACTERISTICS

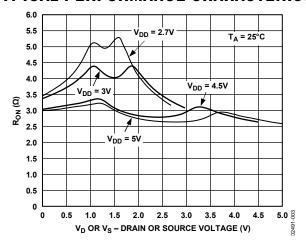


Figure 3. On Resistance as a Function of V_D (V_S) Single Supplies

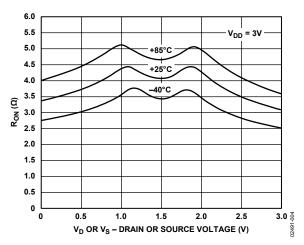


Figure 4. On Resistance as a Function of V_D (V_S) for Different Temperatures $V_{DD} = 3 V$

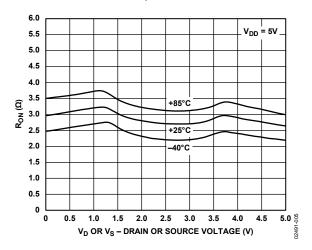


Figure 5. On Resistance as a Function of V_D (V_S) for Different Temperatures $V_{DD} = 5 V$

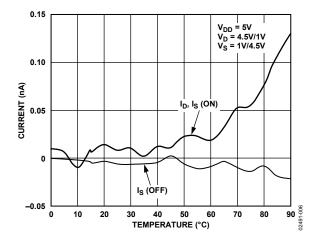


Figure 6. Leakage Currents as a Function of Temperature

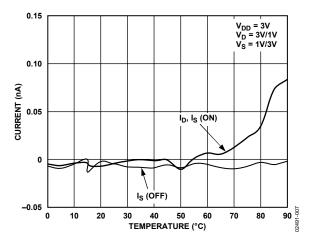


Figure 7. Leakage Currents as a Function of Temperature

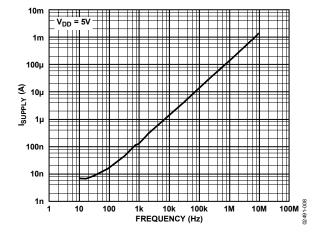


Figure 8. Supply Current vs. Input Switching Frequency

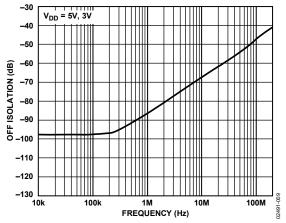


Figure 9. Off Isolation vs. Frequency

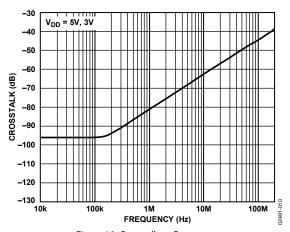


Figure 10. Crosstalk vs. Frequency

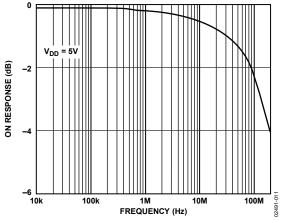
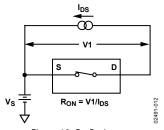
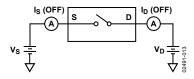


Figure 11. On Response vs. Frequency

TEST CIRCUITS





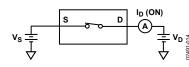
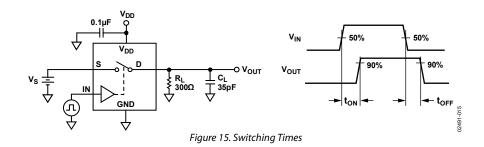


Figure 12. On Resistance

Figure 13. Off Leakage

Figure 14. On Leakage



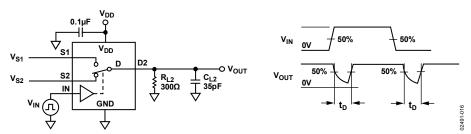


Figure 16. Break-Before-Make Time Delay, t_D

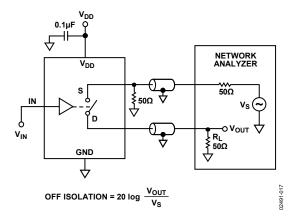


Figure 17. Off Isolation

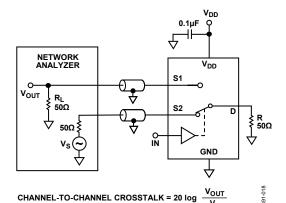


Figure 18. Channel-to-Channel Crosstalk

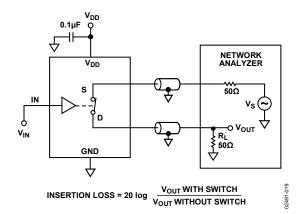
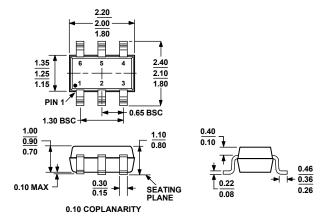


Figure 19. Bandwidth

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-203-AB

Figure 20. 6-Lead Thin Shrink Small Outline Transistor Package [SC70] (KS-6) Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding ¹
ADG779BKS-R2	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SKB
ADG779BKS-REEL	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SKB
ADG779BKS-REEL7	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SKB
ADG779BKSZ-R2 ²	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SOM
ADG779BKSZ-REEL ²	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SOM
ADG779BKSZ-REEL7 ²	-40°C to +85°C	6-Lead Thin Shrink Small Outline Transistor Package (SC70)	KS-6	SOM

¹ Brand on these packages is limited to three characters due to space constraints.



 $^{^{2}}$ Z = Pb-free part.

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MAX4760EWX+T NLAS3799BMNR2G NLAS5123MNR2G NLAS5213AMUTAG NLAS7222AMTR2G MAX14807ECB+
MAX4968ECM+ NLV14066BDG LC78615E-01US-H PI5A4599BCEX PI5A3157BZUEX ADG613SRUZ-EP NLAS4717EPFCT1G
PI5A3167CCEX MAX4744ELB+T MAX4802ACXZ+ DG4051EEN-T1-GE4 SLAS3158MNR2G PI5A3157BC6EX PI5A392AQE
MAX4744HELB+T PI5A4157ZUEX MC74HC4067ADTR2G PI5A4158ZAEX PI5A3166TAEX MAX4901EBL+T MAX14510EEVB+T
PI3A3899ZTEX MAX4996ETG+T MAX4889AETO+T MAX14508EEVB+T MAX4701ETE+T MAX4996LETG+T NLX2G66FCTAG
HI1-5051-2